

OA1161

Gold Bonded Germanium Diode

FEATURES

Low forward voltage drop—low power consumption
Thirty years of proven reliability—one million hours mean time between failures (MTBF)
Very low noise level
Metallurgically bonded

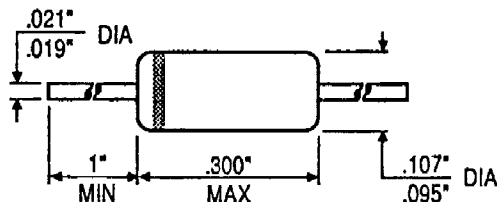
ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

| | |
|---------------------------|------------------|
| Peak Inverse Voltage | 140 Volts |
| Peak Forward Current | 500 mA |
| Operating Temperature | - 65 °C to 85 °C |
| Average Power Dissipation | 80 mW |

ELECTRICAL CHARACTERISTICS

| | Symbol | Conditions | Min | Max | Unit | T °C |
|----------------------|--------|------------|-----|-----|---------|-------|
| Peak Inverse Voltage | PIV | 1 mA | 140 | | V | 25 °C |
| Reverse Current | I_r | 100 V | | 55 | μ A | 25 °C |
| Forward Voltage | V_f | 10 mA | | 1.4 | V | 25 °C |

MECHANICAL



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